

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Cancelled)
2. (Currently amended) A semiconductor laser device, comprising at least two sets of light emitting units and ~~an~~ a polarizing optical element, wherein directions of polarization of ~~for~~ ~~superimposing~~ laser beams emitted from said two sets of light emitting units are deviated from each other and said polarizing optical element superimposes the laser beams emitted from said two sets of light emitting units by reflecting one of the laser beams and by allowing the other of the laser beams to pass, wherein each of said light emitting units comprises a semiconductor laser array for excitation having a plurality of semiconductor laser elements, and an optical resonator having a solid-state laser medium with a reflection mirror formed on one end surface and an output mirror provided in parallel to said reflection mirror, wherein said solid-state laser medium and said output mirror are joined by using a spacer so as to form a gap, and laser beams emitted from the plurality of said semiconductor laser elements enter said optical resonator

independently from each other, and the laser beams are respectively amplified and are projected by said optical resonator.

3. (Currently amended) A semiconductor laser device, comprising a plurality of light emitting units which respectively have at least two sets of light emitting subunits and ~~an~~ a polarizing optical element, wherein directions of polarization of ~~for superimposing~~ laser beams emitted from said two sets of light emitting subunits are deviated from each other and said polarizing optical element superimposes the laser beams emitted from said two sets of light emitting subunits by reflecting one of the laser beams and by allowing the other of the laser beams to pass, wherein ~~said~~ each said subunit ~~subunits~~ comprises a semiconductor laser array for excitation having a plurality of semiconductor laser elements, and an optical resonator having a solid-state laser medium with a reflection mirror formed on one end surface and an output mirror provided in parallel to said reflection mirror, wherein said solid-state laser medium and said output mirror are jointed by using a spacer so as to form a gap, and laser beams emitted from the plurality of said semiconductor laser elements enter said optical resonator independently from each other, and the laser beams are

respectively amplified and are projected by said optical resonator, and wherein laser beams emitted from said light emitting units are respectively projected to optical fibers and the laser beams are joined to a laser beam by bundling said optical fibers.

4. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to~~ claim 2 or 3, wherein a reflection plate is arranged to correspond to the solid-state laser medium, and said output mirror is formed on said reflection plate.

5. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to~~ claim 2 or 3, wherein an optical crystal member for wavelength conversion is provided between said reflection mirror and said output mirror.

6. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to~~ claim 2 or 3, wherein a passive Q-sw element is provided between said reflection mirror and said output mirror.

7. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to~~ claim 2 or 3, wherein an optical crystal

member for wavelength conversion and a passive Q-sw element are provided between said reflection mirror and said output mirror.

8. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to 3~~ claim 2 or 3, wherein said solid-state laser medium is designed in planar shape.

9. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to 3~~ claim 4, wherein said solid-state laser medium and said reflection plate are designed in planar shape and are piled with each other.

10. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to 3~~ claim 5, wherein said solid-state laser medium and said optical crystal member for wavelength conversion are designed in planar shape and are piled with each other.

11. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to 3~~ claim 6, wherein said solid-state laser medium and said passive Q-sw element are designed in planar shape and are piled with each other.

12. (Currently amended) A semiconductor laser device according

to ~~one of claims 1 to 3~~ claim 7, wherein said solid-state laser medium, said optical crystal member for wavelength conversion and said passive Q-sw element are designed in planar shape and are piled with each other.

13. (Cancelled)

14. (Cancelled)

15. (Currently amended) A semiconductor laser device according to claim ~~13~~ 2 or 3, wherein said spacer is a film formed by ~~means such as coating,~~ or vapor deposition.

16. (Currently amended) A semiconductor laser device according to ~~one of claims 1 to~~ claim 2 or 3, wherein said semiconductor laser array for excitation is formed by arranging semiconductor laser elements so that fast axis directions of all laser beams concur with each other, and a rod lens for converging light components of fast axis directions of the laser beams is provided in parallel to said semiconductor laser element array.

17. (Original) A semiconductor laser device according to claim 3, wherein the laser beams emitted from said optical resonator

are joined together by an optical member and are projected into a single optical fiber.